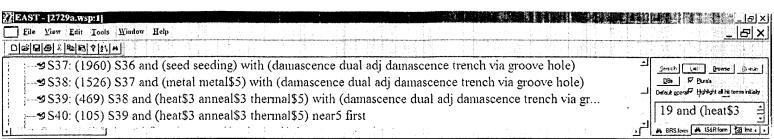
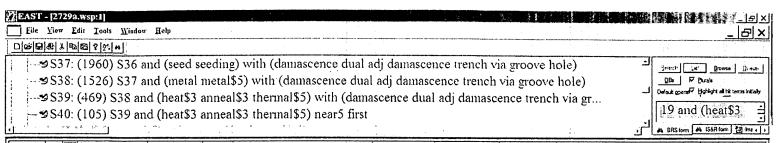


	U	1	Document I	Issue Dat	Page	Title	Current O	Current X Re	etrieval I	nventor	S	C	P	3	3	F
1	Į₹.	Г	US 2005009	2005050	30	Semiconductor device an	438/637		Kunish	ima, Hiroyuk	٣	٦	г	_	П	-
2	Þ	Г	US 2005008	2005042	114	Revolution member supp	204/297.0	204/297.08	Hongo	Akihisa et a	г	٦	г	r	_ I	-
3	P	Г	US 2005004	2005030	19	Chip stack package and	257/678	257/686;	Lee, K	ang-Wook et	Г	г	r.	r	L 1	-
4	F	Г	US 2005000	2005011	10	Semiconductor memory d	257/295	The second secon	Okuno	. Yasutoshi	Г	F	г	Г	T (-
5	Þ	, _	US 2004020	2004102	78	Integrated equipment set	204/229.8	257/E21.5	Li, Hoı	ngwen et al.	٣	٣	r		T	-
6	F	ŗ	US 2004019	2004100	8	Method for forming thick	438/692		Wang,	Sung-Hsiung	٦	Г	Г	ř	r i	-
7	₽	г	US 2004005	2004031	14	Dopant interface formatio	438/162	257/E21.1	Dublin	, Valery M. e	Г	Г	г	г	r (1	-
8	₽	Г	US 2004005	2004031	14	Dopant interface formatio	438/106	257/E21.1	Dubin,	Valery M. et	г	г	г	г	_ I	
9	Þ	Г	US 2004001	2004012	31	Semiconductor device an	438/637		Kunish	ima, Hiroyuk	r	г	7	г	L 1	- :
10	P	г	US 2004000	2004011	75	Integrated equipment set	156/345.1	257/E21.5	Pan, Ju	don Tony et	Г	۲	г	r	- 1	-
11	R	Г	US 2003020	2003103	5	Semiconductor device an	257/750	257/762;	Ueno, l	Kazuyoshi	Γ.	г	r	_		-
12	Þ	г	US 2003016	2003090	 I	Identifying defects in a co	374/5	374/7	Border	ı, Peter G. et	· Γ	г	, r.	_	г г	- 1
13	P	Г.	US 2003007	2003041	42	Integrated equipment set	700/121	257/E21.1	Cheung	g, Robin W.	r	г	г	_	Г (
14	P	Г	US 2003005	2003032	29	Method and apparatus fo	266/81	266/250	Weave	, Robert A.	۲	Г	г	7	Г 1	•
15	P	г	US 2003001	2003011	30	Locally increasing sidewa	438/639	257/E21.2	Apelgr	en, Eric M. e	٢	Г	٦	_	Г; Г	- :
16	Þ	r	US 2003001	2003011	17	Method for manufacturin	204/298.1	257/E21.1	Ueno, l	Kazuyoshi	г	г	г	г	r 1	-
17	P.	г	US 2002007	2002062	19	Method and apparatus fo	205/157	204/274;	Rítzdoi	rf, Thomas L.	Г	Г	Г	r	<u> </u>	- :
18	P.	г	US 2002007	2002061	22	Method of enhancing adh	438/629	257/E21.2	Gilbert	, Stephen R.	Г	٢	r	г	רוו	- :: - :: - ::
19	Þ	٦	US 2002003	2002032	23	Method and apparatus fo	438/618	257/E21.5	Ritzdoi	rf, Thomas L.	Γ.	г		L.	Г	-
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12	р г US 2003016	2003090	Identifying defects in a co	374/5	374/7]	Borden, Peter G. et	г	<u>- </u>		ГГ
13	р Г US 2003007	2003041 42	Integrated equipment set	700/121	257/E21.1	[Cheung, Robin W.	r	г	ГГ	гг
14	р г US 2003005	2003032 29	Method and apparatus fo	266/81	266/250	1	Weaver, Robert A.	г	г	rTr	ГГ
15	₽ F US 2003001	2003011 30	Locally increasing sidewa	438/639	257/E21.2	**************************************	Apelgren, Eric M. e	г	г	r r	ГГ
16	рг US 2003001	2003011 17	Method for manufacturin	204/298.1	257/E21.1		Ueno, Kazuyoshi	г	г	rTr	ГГ
17	рг US 2002007	2002062 19	Method and apparatus fo	205/157	204/274;		Ritzdorf, Thomas L.	г	г	гГг	ГГ
18	₽ r US 2002007	2002061 22	Method of enhancing adh	438/629	257/E21.2	[Gilbert, Stephen R.	г	r	гГ	гг
19	₽ T US 2002003	2002032 23	Method and apparatus fo	438/618	257/E21.5		Ritzdorf, Thomas L.	r.	г	ГГ	ГГ
20	F T US 2002000	2002011 21	Hydrogen-free contact et	438/3	257/E21.0	1	Ma, Shawming et al	۳	r	r	ГГ
21	р г US 2002000	2002010 19	METHOD AND APPAR	148/518	148/536;	1	RITZDORF, THOM	Γ:	r	гГ	rir
22	₽ r US 2001005	2001121 30	Dielectric formation to se	438/597	257/E21.5		Besser, Paul R. et al	Γ,	r	r r	rr
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24	рг US 2001003	2001110 34	Liquid treatment system a	118/70			Nakashima, Satoshi	г	Г	гг	Гг
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26	₽ US 2001003	2001102 22	Hardmask designs for dry	438/396 .	257/E21.0		Moise, Theodore et	г	г	гг	гг
27	೯ г US 2001002	2001092 89	Semiconductor substrate	427/346	156/345.12		Kimura, Norio et al.	г	г	гг	ГГ
28	₽ Г US 6861027	2005030 30	Method and apparatus fo	266/256	118/725	, ,	Weaver; Robert A.	Γ.	r.	ГГ	rir
29	рг US 6841458	2005011 13	Dopant interface formation	438/510	257/E21.1		Dubin; Valery M. et	г	r	r r	ГГ
30	рг US 6753251	4 .	Method for filling recesse		205/157;		Ritzdorf, Thomas L.	г	г	ГГ	ГГ
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Þ	г	US 663	5528	2003102	22	Method of planarizing a c	438/253	257/E21.3		Gilbert; Stephen R.	г	٦			
P	Г	US 663	4370	2003102	32	Liquid treatment system a	134/61	118/500;	Production or standards as a quinter, p. 4.	Nakashima; Satoshi	Г	٦	Г	г	Г¦Г
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P	Г	US 657	6546	2003061	21	Method of enhancing adh	438/629	257/E21.2	and the state of t	Gilbert; Stephen R.	r	г	г	Е	ר ר
₹	Г	US 654	8343	2003041	18	Method of fabricating a f	438/240	438/250;	·	Summerfelt; Scott	٦	Г	Г	7	r r
F	Г	US 653	4809	2003031	22	Hardmask designs for dry	257/295	257/751;	;	Moise; Theodore et	Г	٦	Г	E	r [r.
F	Г	US 651	4844	2003020	29	Sidewall treatment for lo	438/597	257/E21.2	1000000 # 600000000 - 10.00000 #0	Martin; Jeremy I. et	г	Г	г	г	г
F	Г	US 650	8920	2003012	20	Apparatus for low-temper	204/194	118/58;		Ritzdorf; Thomas L.	г	г	[F	Г	СГ
₩	} } r	US 649	2222	2002121	19	Method of dry etching PZ	438/240	438/239;		Xing; Guoqiang	Г	٦	г	Г	٦٦
₽	ŗ	US 648	6063	2002112	13	Semiconductor device ma	438/687 🗸	257/E21.1		Yamasaki; Hideaki	Г	٦	Г	_	ГГ
Þ	Г	US 648	5988	2002112	21	Hydrogen-free contact et	438/3	257/E21.0	; arms r ternans ages on t !	Ma; Shawming et al	٣	г	Г.	Г	ГГ
P	ſ	US 648	2656	2002111	21	Method of electrochemic	438/2	257/E21.1		Lopatin; Sergey	Г	г	г	г	гг
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F	-	US 647	1913	2002102	30	Method and apparatus fo	266/256	118/725;	i i	Weaver; Robert A.	Γ	г	Г	r	Г Г
F	r	US 644	5070	2002090	9	Coherent carbide diffusio	257/751	257/759;	· · · · · · · · · · · · · · · · · · ·	Wang; Pin-Chin Co	Г	r	г	г	г г
P	ŀг	US 636	8967	2002040	31	Method to control mecha	438/687 🗸	257/E21.5		Besser; Paul R.	Г	Г	г	г	ГГ
Þ	-	US 630	3486	2001101	29	Method of fabricating co	438/618	257/374;		Park; Stephen Keet	Г	r.	c	Г	гг
Þ	Г	US 626	1963	2001071	17	Reverse electroplating of	438/704	205/640;	i :	Zhao; Larry et al.	г	г	Г	г	г
Г	٢	US 622	1765	2001042	17	Method for manufacturin	438/653	257/E21.1	**************************************	Ueno; Kazuyoshi	Þ	Г	Г	г	гг
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